Manouchehr Hosseini

List of Publications by Year
in descending order

11 papers	231 citations	1307594 7 h-index	1372567 10 g-index
11 all docs	11 docs citations	11 times ranked	353 citing authors

#	Article	IF	Citations
1	Field-Effect Transistor Based on MoSi$_2$N$_4$ and WSi$_2$N$_4$ Monolayers Under Biaxial Strain: A Computational Study of the Electronic Properties. IEEE Transactions on Electron Devices, 2022, 69, 863-869.	3.0	15
2	A tunable hybrid graphene-metal metamaterial absorber for sensing in the THz regime. Current Applied Physics, 2021, 31, 132-140.	2.4	18
3	A comparative study of substrates disorder on mobility in the Graphene nanoribbon: Charged impurity, surface optical phonon, surface roughness. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 116, 113763.	2.7	15
4	Electrical and electronic properties of strained mono-layer InTe. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 118, 113875.	2.7	15
5	Investigation of Double-Gate Ferroelectric FET Based on Single-Layer MoS2 with Consideration of Contact Resistance. Journal of Electronic Materials, 2020, 49, 4085-4090.	2.2	3
6	Investigation of layer number effects on the electrical properties of strained multi-layer MoS2. Journal of Computational Electronics, 2019, 18, 1236-1242.	2.5	5
7	Strain effects on the DC performance of single-layer TMD-based double-gate field-effect transistors. Journal of Computational Electronics, 2018, 17, 1603-1607.	2.5	7
8	Tunable electromagnetic interference shield using periodic graphene-based structures in the terahertz regime. , 2017, , .		4
9	Very large strain gauges based on single layer MoSe2 and WSe2 for sensing applications. Applied Physics Letters, 2015, 107, .	3.3	32
10	Strain induced mobility modulation in single-layer MoS$_2$. Journal Physics D: Applied Physics, 2015, 48, 375104.	2.8	44
11	Strain-Induced Modulation of Electron Mobility in Single-Layer Transition Metal Dichalcogenides MX$_2$ (<inline-formula> <tex-math notation="LaTeX">$M = {m Mo}$) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf Electron Devices, 2015, 62, 3192-3198.	3.0	73